Gabriel Ferro

List of Publications by Citations

158 papers	1,401 citations	21 h-index	31 g-index
174 ext. papers	1,533 ext. citations	1.7 avg, IF	4.34 L-index

#	Paper	IF	Citations
158	A Vapor–liquid–Solid Mechanism for Growing 3C-SiC Single-Domain Layers on 6H-SiC(0001). *Advanced Functional Materials*, **2006**, 16, 975-979	15.6	77
157	Evidence for Flat Bands near the Fermi Level in Epitaxial Rhombohedral Multilayer Graphene. *ACS Nano*, **2015**, 9, 5432-9	16.7	69
156	3C-SiC Heteroepitaxial Growth on Silicon: The Quest for Holy Grail. *Critical Reviews in Solid State and Materials Sciences*, **2015**, 40, 56-76	10.1	52
155	Growth by a vapour–liquid–solid mechanism: a new approach for silicon carbide epitaxy. *New Journal of Chemistry*, **2004**, 28, 889-896	3.6	52
154	Photonic crystal cavities in cubic (3C) polytype silicon carbide films. *Optics Express*, **2013**, 21, 32623-9	3.3	50
153	Critically coupled surface phonon-polariton excitation in silicon carbide. *Optics Letters*, **2009**, 34, 2667-9	3	45
152	A comprehensive study of SiC growth processes in a VPE reactor. *Thin Solid Films*, **2002**, 402, 83-89	2.2	43
151	Midinfrared Index Sensing of pL-Scale Analytes Based on Surface Phonon Polaritons in Silicon Carbide. *Journal of Physical Chemistry C*, **2010**, 114, 7489-7491	3.8	39
150	Vapor–liquid–Solid Growth of 3C-SiC on 4H-SiC Substrates. 1. Growth Mechanism. *Crystal Growth and Design*, **2008**, 8, 1044-1050	3.5	38
149	Direct synthesis of β-SiC and h-BN coated β-SiC nanowires. *Solid State Communications*, **2002**, 124, 157-161	1.6	38
148	Hybrid Group IV Nanophotonic Structures Incorporating Diamond Silicon-Vacancy Color Centers. *Nano Letters*, **2016**, 16, 212-7	11.5	35
147	Strain Tailoring in 3C-SiC Heteroepitaxial Layers Grown on Si(100). *Chemical Vapor Deposition*, **2006**, 12, 483-488		35
146	Nanodiamond Integration with Photonic Devices. *Laser and Photonics Reviews*, **2019**, 13, 1800316	8.3	32
145	Visible Photoluminescence from Cubic (3C) Silicon Carbide Microdisks Coupled to High Quality Whispering Gallery Modes. *ACS Photonics*, **2015**, 2, 14-19	6.3	31
144	Measurements of the negative refractive index of sub-diffraction waves propagating in an indefinite permittivity medium. *Optics Express*, **2010**, 18, 22734-46	3.3	30
143	Characterization of a 3C-SiC Single Domain Grown on 6H-SiC(0001) by a Vapor–liquid–Solid Mechanism. *Crystal Growth and Design*, **2006**, 6, 2598-2602	3.5	27
142	On the growth of 4H-SiC by low-temperature liquid phase epitaxy in Al rich Al–Si melts. *Journal of Crystal Growth*, **2003**, 254, 123-130	1.6	26

141	Highly confined hybrid spoof surface plasmons in ultrathin metal-dielectric heterostructures. *Physical Review Letters*, **2010**, 105, 176803	7.4	24
140	Nucleation of 3C□SiC on 6H□SiC from a liquid phase. *Acta Materialia*, **2007**, 55, 6873-6880	8.4	24
139	A Study on the Temperature of Ohmic Contact to p-Type SiC Based on Ti3SiC2 Phase. *IEEE Transactions on Electron Devices*, **2016**, 63, 2462-2468	2.9	22
138	From Si nanowire to SiC nanotube. *Journal of Nanoparticle Research*, **2011**, 13, 5425-5433	2.3	22
137	How to Grow Unstrained 3C-SiC Heteroepitaxial Layers on Si (100) Substrates. *Materials Science Forum*, **2001**, 353-356, 155-158	0.4	21
136	Very Low Interface State Density From Thermally Oxidized Single-Domain 3C□SiC/6H□SiC Grown by Vapour□Liquid□Solid Mechanism. *Japanese Journal of Applied Physics*, **2006**, 45, 6823-6829	1.4	18
135	Sublimation Growth and Structural Characterization of 3C-SiC on Hexagonal and Cubic SiC Seeds. *Materials Science Forum*, **2010**, 645-648, 175-178	0.4	16
134	Improved Ni/3C-SiC contacts by effective contact area and conductivity increases at the nanoscale. *Applied Physics Letters*, **2009**, 94, 112104	3.4	16
133	Study of the 3C-SiC nucleation from a liquid phase on a C face 6H-SiC substrate. *Journal of Crystal Growth*, **2009**, 311, 2385-2390	1.6	16
132	RHEED monitoring of AlN epitaxial growth by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2000**, 210, 429-434	1.6	16
131	Vapor□Liquid□Solid Growth of 3C-SiC on □SiC Substrates. 2. Growth Kinetics. *Crystal Growth and Design*, **2008**, 8, 1051-1054	3.5	15
130	Flash Lamp Supported Deposition of 3C-SiC (FLASiC) □ a Promising Technique to Produce High Quality Cubic SiC Layers. *Materials Science Forum*, **2004**, 457-460, 175-180	0.4	14
129	The (001) 3C SiC surface termination and band structure after common wet chemical etching procedures, stated by XPS, LEED, and HREELS. *Applied Surface Science*, **2018**, 427, 480-485	6.7	14
128	A new model for in situ nitrogen incorporation into 4H-SiC during epitaxy. *Scientific Reports*, **2017**, 7, 43069	4.9	13
127	Buried Selective Growth of p-Doped SiC by VLS Epitaxy. *Materials Science Forum*, **2012**, 717-720, 169-172	0.4	13
126	Growth mode of AlN epitaxial layers on 6H-SiC by plasma assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2000**, 209, 415-418	1.6	13
125	Deposition of nanocrystalline translucent h-BN films by chemical vapor deposition at high temperature. *Thin Solid Films*, **2012**, 520, 2424-2428	2.2	12
124	Overview of 3C-SiC Crystalline Growth. *Materials Science Forum*, **2010**, 645-648, 49-54	0.4	12

123	Ge incorporation inside 4H-SiC during homoepitaxial growth by chemical vapor deposition. *Acta Materialia*, **2014**, 75, 219-226	8.4	11
122	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. *Materials Science Forum*, **2014**, 778-780, 706-709	0.4	11
121	SiC Homoepitaxial Growth at Low Temperature by Vapor–Liquid–Solid Mechanism in Al–Si Melt. *Crystal Growth and Design*, **2003**, 3, 285-287	3.5	11
120	Effect of the Si Droplet Size on the VLS Growth Mechanism of SiC Homoepitaxial Layers. *Materials Science Forum*, **2002**, 389-393, 287-290	0.4	10
119	Growth of silicon oxide nanowires at low temperature using tin hydroxide catalyst. *Journal of Crystal Growth*, **2011**, 320, 55-62	1.6	9
118	Aluminium-Silicon as a Melt for the Low Temperature Growth of SiC Crystals. *Materials Science Forum*, **2001**, 353-356, 85-90	0.4	9
117	Growth Mode and Kinetics of Atmospheric Pressure Chemical Vapour Deposition of β-SiC on Si(100) Substrate. *Materials Science Forum*, **1998**, 264-268, 227-230	0.4	9
116	Two-dimensional defect mapping of the SiO2/4H-SiC interface. *Physical Review Materials*, **2019**, 3,	3.2	9
115	AlN hollow-nanofilaments by electrospinning. *Nanotechnology*, **2015**, 26, 085603	3.4	8
114	Searching for Ge Clusters inside 3C-SiC Layers Grown by Vapor-Liquid-Solid Mechanism on 6H-SiC Substrates. *Materials Science Forum*, **2009**, 615-617, 185-188	0.4	8
113	Incorporation of group III, IV and V elements in 3C-SiC(111) layers grown by the vapour–liquid–solid mechanism. *Journal of Crystal Growth*, **2010**, 312, 3443-3450	1.6	8
112	Optical Investigation of Cubic SiC Layers Grown on Hexagonal SiC Substrates by CVD and VLS. *Materials Science Forum*, **2007**, 556-557, 403-406	0.4	8
111	Growth and Characterisation of Heavily Al-Doped 4H-SiC Layers Grown by VLS in an Al-Si Melt. *Materials Science Forum*, **2004**, 457-460, 735-738	0.4	8
110	Improved SiCOI Structures Elaborated by Heteroepitaxy of 3C-SiC on SOI. *Materials Science Forum*, **2002**, 389-393, 343-346	0.4	8
109	Characterization of Ge-Doped Homoepitaxial Layers Grown by Chemical Vapor Deposition. *Materials Science Forum*, **2014**, 778-780, 261-264	0.4	7
108	Electrical Characterization of PiN Diodes with p+ Layer Selectively Grown by VLS Transport. *Materials Science Forum*, **2013**, 740-742, 911-914	0.4	7
107	Nanoscale probing of dielectric breakdown at SiO2/3C-SiC interfaces. *Journal of Applied Physics*, **2011**, 109, 013707	2.5	7
106	On the Mechanism of Twin Boundary Elimination in 3C-SiC(111) Heteroepitaxial Layers on 4H-SiC Substrates. *Materials Science Forum*, **2011**, 679-680, 71-74	0.4	7

105	Probing the effect of temperature on the incorporation of Al species in a SiC matrix. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1265-1268		7
104	Prism-coupled surface wave accelerator based on silicon carbide. *Physical Review Special Topics: Accelerators and Beams*, **2012**, 15,		6
103	Optical Characterization of VLS+CVD Grown 3C-SiC Films by Non-Linear and Photoluminescence Techniques. *Materials Science Forum*, **2010**, 645-648, 443-446	0.4	6
102	Investigation of 3C-SiC(111) Homoepitaxial Growth by CVD at High Temperature. *Materials Science Forum*, **2010**, 645-648, 127-130	0.4	6
101	Low Doped 3C-SiC Layers Deposited by the Vapour-Liquid-Solid Mechanism on 6H-SiC Substrates. *Materials Science Forum*, **2010**, 645-648, 171-174	0.4	6
100	Detailed study of the influence of surface misorientation on the density of Anti-Phase Boundaries in 3C-SiC layers grown on (001) silicon **2010**,		6
99	MOS Capacitors Fabricated on 3C-SiC(111) Layers Grown on 6H-SiC(0001). *Journal of the Electrochemical Society*, **2011**, 158, H630	3.9	6
98	Optical Study of Ge Incorporation in Cubic SiC Layers Grown by VLS. *Materials Science Forum*, **2008**, 600-603, 529-532	0.4	6
97	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. *Materials Science Forum*, **2006**, 527-529, 287-290	0.4	6
96	Growth of SiC from a Liquid Phase at Low Temperature. *Materials Science Forum*, **2007**, 556-557, 41-46	0.4	6
95	Ge Assisted SiC Epitaxial Growth by CVD on SiC Substrate. *Materials Science Forum*, **2014**, 778-780, 187-192	0.4	5
94	Is the Liquid Phase a Viable Approach for Bulk Growth of 3C-SiC?. *Materials Science Forum*, **2010**, 645-648, 67-70	0.4	5
93	3C-SiC MOS Based Devices: From Material Growth to Device Characterization. *Materials Science Forum*, **2011**, 679-680, 433-436	0.4	5
92	Evolution of 3C-SiC islands nucleated from a liquid phase on Si face □SiC substrates. *Thin Solid Films*, **2010**, 518, 4234-4241	2.2	5
91	Checker-Board Carbonization for Control and Reduction of the Mean Curvature of 3C-SiC Layers Grown on Si(100) Substrates. *Materials Science Forum*, **2004**, 457-460, 265-268	0.4	5
90	Investigation of Thick 3C-SiC Films Re-Grown on Thin 35 nm "Flash Lamp Annealed" 3C-SiC Layers. *Materials Science Forum*, **2004**, 457-460, 313-316	0.4	5
89	Nature effect of the gas during high temperature treatments of 4H-SiC substrates. *Applied Surface Science*, **2003**, 207, 200-207	6.7	5
88	Microstructural Characterization of 3C-SiC Thin Films Grown by Flash Lamp Induced Liquid Phase Epitaxy. *Materials Science Forum*, **2005**, 483-485, 295-298	0.4	5

87	Comparative Evaluation of Free-Standing 3C-SiC Crystals. *Materials Science Forum*, **2005**, 483-485, 229-232	0.4	5
86	Development and Characterization of Inorganic Scintillating Fibers Made of LuAG:Ce and LYSO:Ce. *IEEE Transactions on Nuclear Science*, **2014**, 61, 353-361	1.7	4
85	Boron Doping during Vapor-Liquid-Solid Growth of Homoepitaxial 4H-SiC Layers. *Materials Science Forum*, **2007**, 556-557, 65-68	0.4	4
84	Structural Characterization of Thin 3C-SiC Films Annealed by the Flash Lamp Process. *Materials Science Forum*, **2004**, 457-460, 351-354	0.4	4
83	Is the Al Solubility Limit in SiC Temperature Dependent or not?. *Materials Science Forum*, **2005**, 483-485, 125-128	0.4	4
82	Electrical Characterisation of Heavily Al Doped 4H-SiC Layer Grown by Vapour-Liquid-Solid Epitaxy in Al-Si Melt. *Materials Science Forum*, **2005**, 483-485, 421-424	0.4	4
81	Silicon Deposition on 3C-SiC Seeds of Different Orientations. *Materials Science Forum*, **2017**, 897, 87-90	0.4	3
80	Growth of aluminum nitride on flat and patterned Si (111) by high temperature halide CVD. *Thin Solid Films*, **2017**, 623, 65-71	2.2	3
79	A Study on the Chemistry of Epitaxial Ti3SiC2 Formation on 4H-SiC Using Al-Ti Annealing. *Materials Science Forum*, **2015**, 821-823, 432-435	0.4	3
78	Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts. *Materials Science Forum*, **2014**, 778-780, 639-644	0.4	3
77	Investigation of 3C-SiC growth on Si(111) by vapor□quid□olid transport using a SiGe liquid phase. *Journal of Crystal Growth*, **2012**, 354, 119-128	1.6	3
76	p-Doped SiC Growth on Diamond Substrate by VLS Transport. *Materials Science Forum*, **2013**, 740-742, 331-334	0.4	3
75	Growing 3C-SiC heteroepitaxial layers on □SiC substrate by vapour□quid□olid mechanism from the Al□e□i ternary system. *Journal of Crystal Growth*, **2011**, 318, 397-400	1.6	3
74	Further Evidence of Nitrogen Induced Stabilization of 3C-SiC Polytype during Growth from a Si-Ge Liquid Phase. *Materials Science Forum*, **2010**, 645-648, 163-166	0.4	3
73	Growth of Nanocrystalline Translucent h-BN Films Deposited by CVD at High Temperature on SiC Substrates. *Materials Science Forum*, **2010**, 645-648, 1191-1194	0.4	3
72	Influence of the C/Si Ratio on the Dopant Concentration and Defects in CVD Grown 3C-SiC Homoepitaxial Layers **2010**,		3
71	Effect of the Crystallization Conditions on the Epitaxial Relationship of Si Deposited on 3C-SiC(100). *Materials Science Forum*, **2006**, 527-529, 1563-1566	0.4	3
70	How to Grow 3C-SiC Single Domain on □SiC(0001) by Vapor-Liquid-Solid Mechanism. *Materials Science Forum*, **2007**, 556-557, 187-190	0.4	3

69	Interfacial Strain and Defects in Si (001) Carbonization Layers for 3C-SiC Hetero-Epitaxy. *Materials Science Forum*, **2004**, 457-460, 277-280	0.4	3
68	Understanding Al incorporation into 4H-SiC during epitaxy. *Journal of Crystal Growth*, **2019**, 507, 338-343	1.6	3
67	Analysis of 4H-SiC MOS Capacitors on Macro-Stepped Surfaces. *Materials Science Forum*, **2017**, 897, 107-110	0.4	2
66	On the Formation of Graphene by Ge Intercalation of a 4H-SiC Surface. *Materials Science Forum*, **2015**, 821-823, 961-964	0.4	2
65	Optimization of VLS Growth Process for 4H-SiC P/N Junctions. *Materials Science Forum*, **2016**, 858, 205-208	0.4	2
64	Influence of Ga doping on the microstructure of 3C-SiC layers grown on 4H-SiC substrates by VLS mechanism. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 72-75		2
63	Highly Mg-doped GaN dots and films grown by VLS transport at low temperature. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600428	1.6	2
62	Properties of 3C-SiC Grown by Sublimation Epitaxy on Different Type of Substrates. *Materials Science Forum*, **2010**, 645-648, 183-186	0.4	2
61	LTPL Investigation of N-Ga and N-Al Donor-Acceptor Pair Spectra in 3C-SiC Layers Grown by VLS on 6H-SiC Substrates. *Materials Science Forum*, **2010**, 645-648, 415-418	0.4	2
60	Defects in (111) 3C-SiC layers grown at different temperatures by VLS and CVD on 6H-SiC substrates **2010**,		2
59	Elaboration and characterization of boron doping during SiC growth by VLS mechanism. *Journal of Crystal Growth*, **2011**, 327, 46-51	1.6	2
58	Investigation of 3C-SiC Lateral Growth on 4H-SiC Mesas. *Materials Science Forum*, **2011**, 679-680, 111-114	0.4	2
57	Influence of Post-Growth Annealing on the Defects Nature and Distribution in VLS Grown (111) 3C-SiC Layers. *Materials Science Forum*, **2011**, 679-680, 241-244	0.4	2
56	Seeding Layer Influence on the Low Temperature Photoluminescence Intensity of 3C-SiC Grown on 6H-SiC by Sublimation Epitaxy. *Materials Science Forum*, **2012**, 711, 149-153	0.4	2
55	Surface Morphology Evolution after Epitaxial Growth on 4° Off-Axis 4H-SiC Substrate. *Materials Science Forum*, **2012**, 717-720, 145-148	0.4	2
54	Formation of 3C-SiC Films Embedded in SiO2 by Sacrificial Oxidation. *Materials Science Forum*, **2004**, 457-460, 1515-1518	0.4	2
53	Analysis of SiC Islands Formation during First Steps of Si Carbonization Process. *Materials Science Forum*, **2005**, 483-485, 555-558	0.4	2
52	SiO2 as Oxygen Source for the Chemical Vapor Transport of SiC. *Materials Science Forum*, **2002**, 389-393, 307-310	0.4	2

51	4H-SiC(0001) Surface Faceting during Interaction with Liquid Si. *Materials Science Forum*, **2016**, 858, 163-166	0.4	2
50	VLS Grown 4H-SiC Buried P+ Layers for JFET Lateral Structures. *Materials Science Forum*, **2015**, 821-823, 789-792	0.4	1
49	Characterization and Applications of New High Quality LuAG:Ce and LYSO:Ce fibers. *Journal of Physics: Conference Series*, **2015**, 587, 012067	0.3	1
48	Visible Photoluminescence in Cubic (3C) Silicon Carbide Coupled to High Quality Microdisk Resonators **2015**,		1
47	Understanding of the Growth Mechanism Leading to Twin Boundary Elimination during 3C-SiC Heteroepitaxy on 4H-SiC Substrate by CVD. *Materials Science Forum*, **2015**, 821-823, 209-212	0.4	1
46	MOS Interface Characteristics of In Situ Ge-Doped 4H-SiC Homoepitaxial Layers. *Materials Science Forum*, **2015**, 821-823, 512-515	0.4	1
45	Characterization and optimization of new high-quality inorganic fibers made of LuAG:Ce and LYSO:Ce **2014**,		1
44	Heteroepitaxial CVD Growth of 3C-SiC on Diamond Substrate. *Materials Science Forum*, **2014**, 778-780, 226-229	0.4	1
43	Study of the Nucleation of p-Doped SiC in Selective Epitaxial Growth Using VLS Transport. *Materials Science Forum*, **2013**, 740-742, 177-180	0.4	1
42	TEM and LTPL Investigations of 3C-SiC Layers Grown by LPE on (100) and (111) 3C-SiC Seeds. *Materials Science Forum*, **2010**, 645-648, 383-386	0.4	1
41	Reliability of Thin Thermally Grown SiO2 on 3C-SiC Studied by Scanning Probe Microscopy. *Materials Science Forum*, **2010**, 645-648, 833-836	0.4	1
40	Deep levels in hetero-epitaxial as-grown 3C-SiC **2010**,		1
39	Effect of nitrogen impurity on the stabilization of 3C-SiC polytype during heteroepitaxial growth by vapor–liquid–solid mechanism on 6H-SiC substrates. *Diamond and Related Materials*, **2011**, 20, 808-813	3.5	1
38	Defect-induced polytype transformations in LPE grown SiC epilayers on (1 1 1) 3C-SiC seeds grown by VLS on 6H-SiC. *Physica B: Condensed Matter*, **2009**, 404, 4727-4730	2.8	1
37	Investigation of the Growth of 3C-SiC on Si by Vapor-Liquid-Solid (VLS) Transport. *Materials Science Forum*, **2011**, 679-680, 99-102	0.4	1
36	New Approaches to In Situ Doping of SiC Epitaxial Layers. *Advanced Materials Research*, **2011**, 324, 14-19	0.5	1
35	Nondestructive Evaluation of Photo-Electrical Properties of 3C-SiC (111) Homoepitaxial Layers Grown by CVD. *Materials Science Forum*, **2011**, 679-680, 153-156	0.4	1
34	On Applicability of Time-Resolved Optical Techniques for Characterization of Differently Grown 3C-SiC Crystals and Heterostructures. *Materials Science Forum*, **2012**, 711, 159-163	0.4	1

33	Using Vapour-Liquid-Solid Mechanism for SiC Homoepitaxial Growth on on-axis 6H-SiC (0001) at Low Temperature. *Materials Science Forum*, **2006**, 527-529, 271-274	0.4	1
32	Control of the 2D/3D Transition of Cubic GaN/AlN Nanostructures on 3C-SiC Epilayers. *Materials Science Forum*, **2004**, 457-460, 1561-1564	0.4	1
31	Comparison of Different Metal Additives to Si for the Homoepitaxial Growth of 4H-SiC Layers by Vapour-Liquid-Solid Mechanism. *Materials Science Forum*, **2004**, 457-460, 245-248	0.4	1
30	Growth and doping of silicon carbide with germanium: a review. *Critical Reviews in Solid State and Materials Sciences*,1-18	10.1	1
29	Optimization of the Silicidation and Growth Processes for 3C-SiC Heteroepitaxy on Diamond Substrate. *Materials Science Forum*, **2016**, 858, 155-158	0.4	1
28	Growth and Characterization of Undoped Polysilicon Thick Layers: Revisiting an Old System. *Silicon*, **2020**, 12, 1187-1194	2.4	1
27	Low temperature homoepitaxy of GaN structures by Vapor Liquid Solid transport. *Journal of Crystal Growth*, **2017**, 467, 18-28	1.6	0
26	Very High Sustainable Forward Current Densities on 4H-SiC p-n Junctions Formed by VLS Localized Epitaxy of Heavily Al-Doped p++ Emitters. *Materials Science Forum*, **2017**, 897, 63-66	0.4	0
25	Behavior and Chemical Reactions of Liquid Si and Ge on Si3N4 Surface. *Materials Science Forum*, **2015**, 821-823, 121-124	0.4	0
24	How to Grow Fully (100) Oriented SiC/Si/SiC/Si Multi-Stack. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800588	1.6	
23	Ge Addition during 4H-SiC Epitaxial Growth by CVD: Mechanism of Incorporation. *Materials Science Forum*, **2015**, 821-823, 115-120	0.4	
22	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. *Materials Science Forum*, **2015**, 821-823, 424-427	0.4	
21	Thermally Stable Ohmic Contact to p-Type 4H-SiC Based on Ti3SiC2 Phase. *Materials Science Forum*, **2016**, 858, 553-556	0.4	
20	Ge Assisted 3C-SiC Nucleation and Growth by Vapour Phase Epitaxy on On-Axis 4H-SiC Substrate. *Materials Science Forum*, **2014**, 806, 27-31	0.4	
19	3C-SiC Seeded Growth on Diamond Substrate by VLS Transport. *Materials Science Forum*, **2014**, 778-780, 234-237	0.4	
18	Heteroepitaxy of P-Doped 3C-SiC on Diamond by VLS Transport. *Materials Science Forum*, **2014**, 806, 33-37	0.4	
17	Improvement of the Specific Contact Resistance on P-Type 4H-SiC by Using a Highly P-Typed Doped 4H-SiC Layer Selectively Grown by VLS Transport. *Materials Science Forum*, **2014**, 806, 57-60	0.4	
16	Elaboration of Core Si/Shell SiC Nanowires. *Materials Science Forum*, **2013**, 740-742, 306-310	0.4	

15	Exploring SiC Growth Limitation of Vapor-Liquid-Solid Mechanism when Using Two Different Carbon Precursors. *Materials Science Forum*, **2013**, 740-742, 323-326	0.4
14	On the Characterization of Boron in BGaAs Nano-Films Using IBA Techniques. *Advanced Materials Research*, **2011**, 324, 314-317	0.5
13	Nano-Electro-Structural Evolution of Ni-Si Ohmic Contacts to 3C-SiC. *Materials Science Forum*, **2009**, 615-617, 569-572	0.4
12	Effects of Temperature and Heating Rate on the Precipitation of 3C-SiC Islands on 4H-SiC(0001) from a Liquid Phase. *Materials Science Forum*, **2009**, 615-617, 193-196	0.4
11	On the Quantification of Al Incorporated in SiC Material Using Particle Induced X-Ray Emission Technique. *Materials Science Forum*, **2011**, 679-680, 189-192	0.4
10	On the Characterization of Ultra Thin Al Films Deposited onto SiC Substrate Using PIXE Technique. *Advanced Materials Research*, **2011**, 324, 302-305	0.5
9	Structural and Optical Investigation of VLS Grown (111) 3C-SiC Layers on 6H-SiC Substrates in Sn-Based Melts. *Materials Science Forum*, **2011**, 679-680, 165-168	0.4
8	Epitaxial Growth of 3C-SiC onto Silicon Substrate by VLS Transport Using CVD-Grown 3C-SiC Seeding Layer. *Materials Science Forum*, **2012**, 711, 35-39	0.4
7	Elimination of Twin Boundaries when Growing 3C-SiC Heteroepitaxial by Vapour-Liquid-Solid Mechanism on Patterned 4H-SiC Substrate. *Materials Science Forum*, **2012**, 711, 11-15	0.4
6	Study of the Lateral Growth by VLS Mechanism Using Al-Based Melts on Patterned SiC Substrate. *Materials Science Forum*, **2012**, 717-720, 165-168	0.4
5	Potential of HMDS/C3H8 Precursor System for the Growth of State of the Art Heteroepitaxial 3C-SiC Layers on Si(100). *Materials Science Forum*, **2004**, 457-460, 281-284	0.4
4	Planar Defects, Voids and their Relationship in 3C-SiC Layers. *Materials Science Forum*, **2005**, 483-485, 189-192	0.4
3	3C-SiC Microdisks for Visible Photonics. *Materials Science Forum*, **2016**, 858, 711-714	0.4
2	Silicon (001) Heteroepitaxy on 3C-SiC(001)/Si(001) Seed. *Materials Science Forum*, **2018**, 924, 128-131	0.4
1	Liquid Si-Induced 4H-SiC Surface Structuring Using a Sandwich Configuration. *Materials Science Forum*,1062, 8-12	0.4